



Description

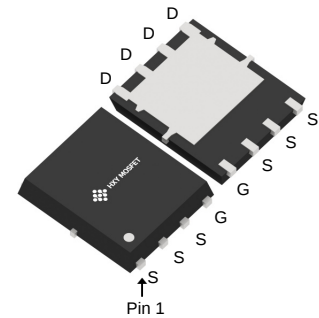
The SI7848BDP-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

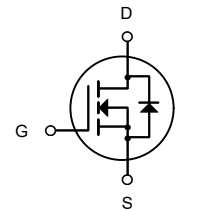
$V_{DS} = 40V$ $I_D = 55A$
 $R_{DS(ON)} < 8.5m\Omega$ $V_{GS}=10V$

Application

Battery protection
Load switch
Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI7848BDP-T1-GE3	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	55	A
$I_D@T_c=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	41	A
I_{DM}	Pulsed Drain Current ²	280	A
EAS	Single Pulse Avalanche Energy ³	76	mJ
T_{STG}	Storage Temperature Range	-55 to 175	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 175	$^{\circ}C$



Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=15A$	---	7.5	8.5	$m\Omega$
		$V_{GS}=4.5V$, $I_D=8A$	---	9	12	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.8	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=40V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.0	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V$, $V_{GS}=10V$, $I_D=10A$	---	19.7	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	5.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	13.2	---	ns
T_r	Rise Time		---	2.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	72	---	
T_f	Fall Time		---	4.5	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	6000	---	pF
C_{oss}	Output Capacitance		---	1509	---	
C_{rss}	Reverse Transfer Capacitance		---	129	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	140	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=31A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

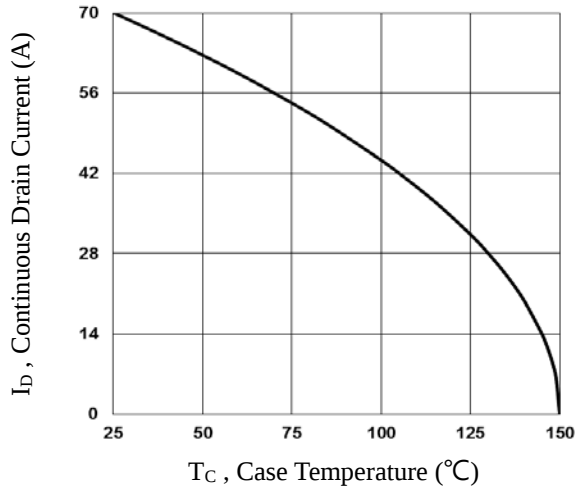


Fig.1 Continuous Drain Current vs. T_C

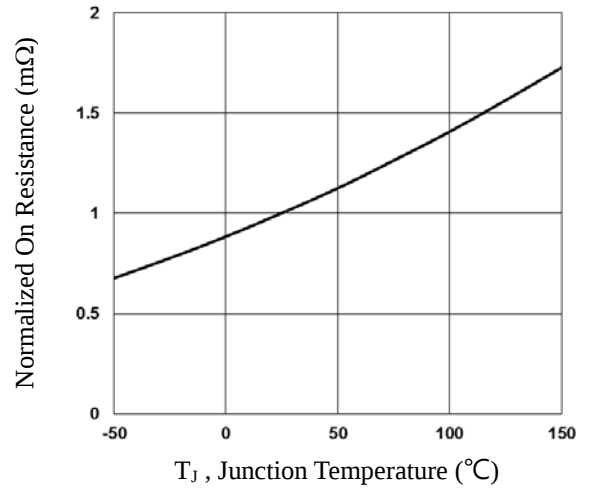


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

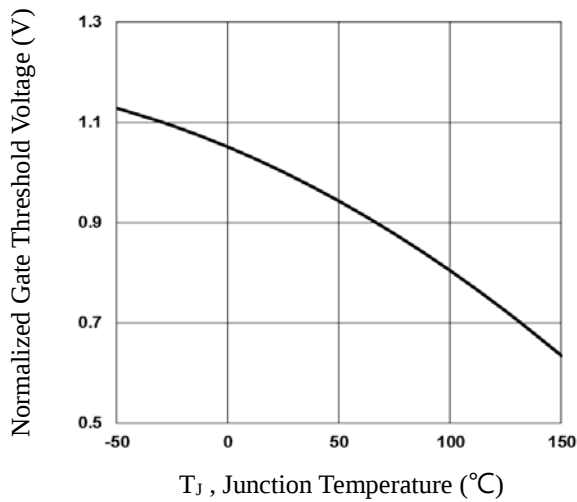


Fig.3 Normalized V_{th} vs. T_J

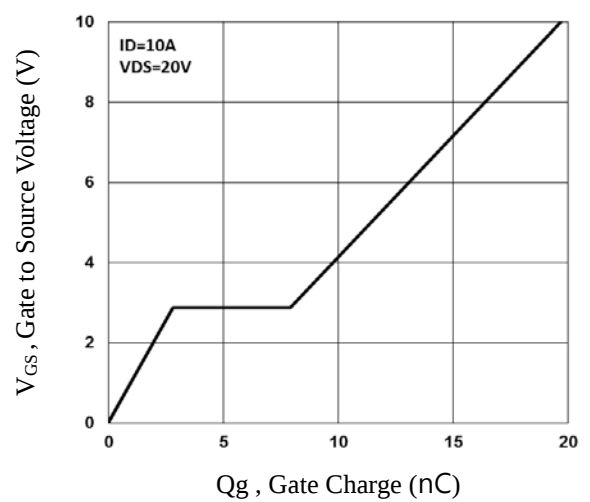


Fig.4 Gate Charge Waveform

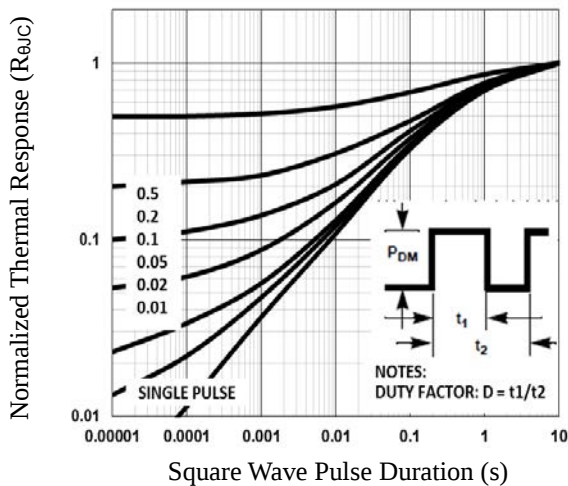


Fig.5 Normalized Transient Impedance

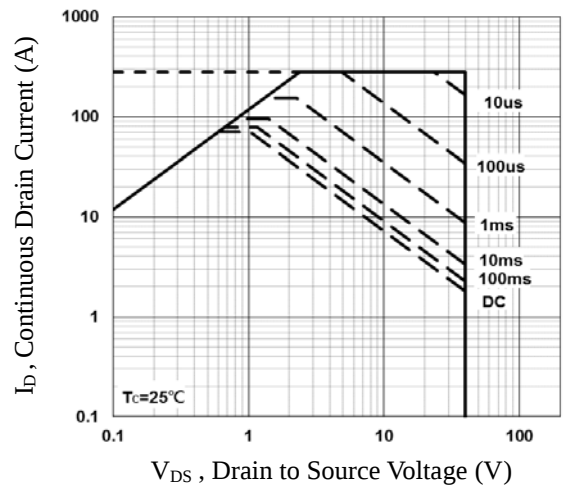


Fig.6 Maximum Safe Operation Area

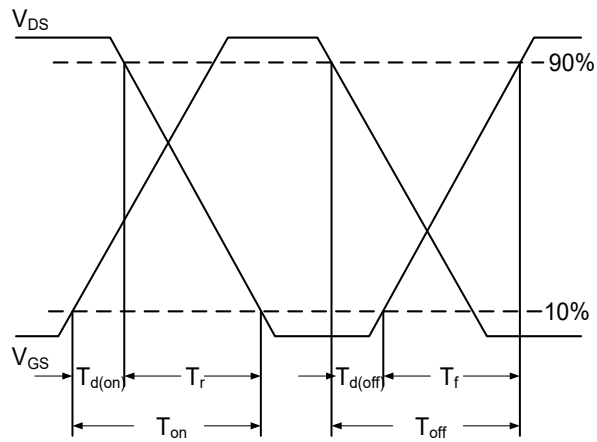


Fig.7 Switching Time Waveform

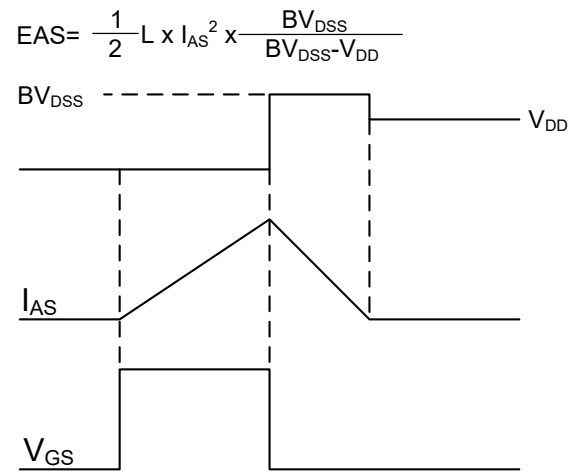
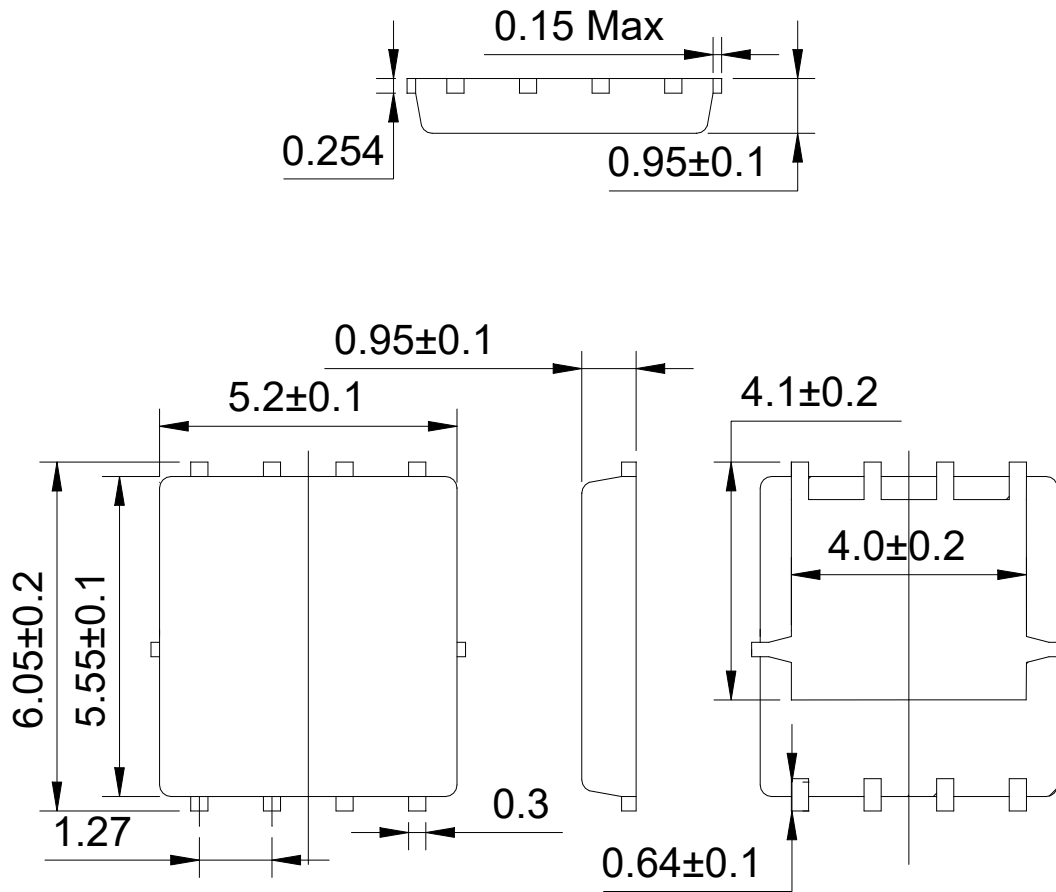


Fig.8 EAS Waveform



DFN5X6-8L Package Information

Unit:mm





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